

Ordering number : ENN6900

P-Channel Silicon MOSFET



**MCH3306**

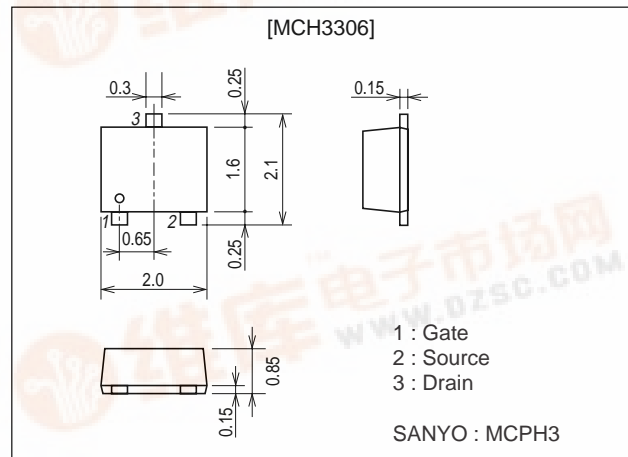
**Ultrahigh-Speed Switching Applications**

**Features**

- Low ON-resistance.
- Ultrahigh-speed switching.
- 1.8V drive.

**Package Dimensions**

unit : mm  
2167



**Specifications**

**Absolute Maximum Ratings** at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		-20	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±10	V
Drain Current (DC)	I <sub>D</sub>		-2	A
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	-8	A
Allowable Power Dissipation	P <sub>D</sub>	Mounted on a ceramic board (900mm <sup>2</sup> X0.8mm)	1	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

**Electrical Characteristics** at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> =-1mA, V <sub>GS</sub> =0	-20			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-20V, V <sub>GS</sub> =0			-10	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-1mA	-0.3		-1.0	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-1A	2.1	3.0		S
Static Drain-to-Source On-State Resistance	R <sub>DS(on)1</sub>	I <sub>D</sub> =-1A, V <sub>GS</sub> =-4V		110	145	mΩ
	R <sub>DS(on)2</sub>	I <sub>D</sub> =-0.5A, V <sub>GS</sub> =-2.5V		140	200	mΩ
	R <sub>DS(on)3</sub>	I <sub>D</sub> =-0.1A, V <sub>GS</sub> =-1.8V		180	260	mΩ

Marking : JF

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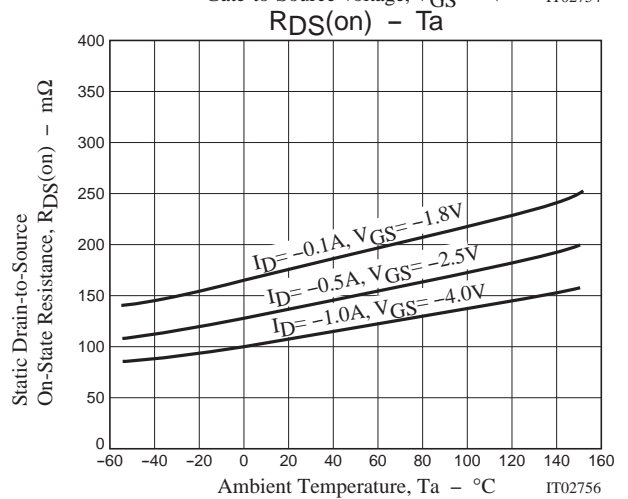
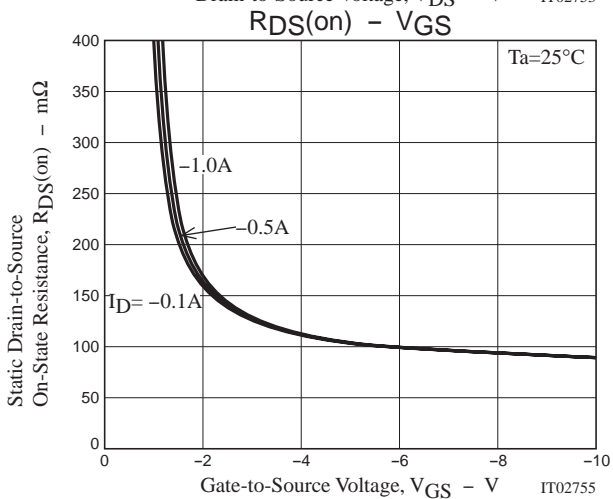
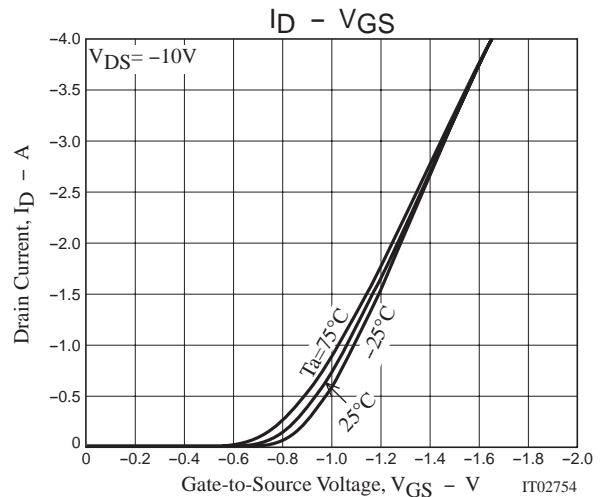
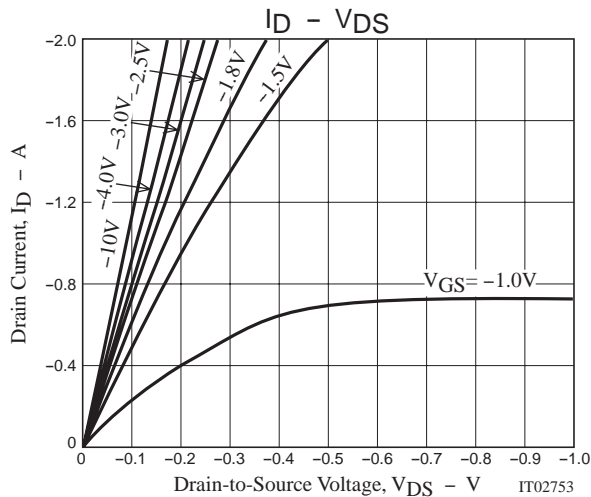
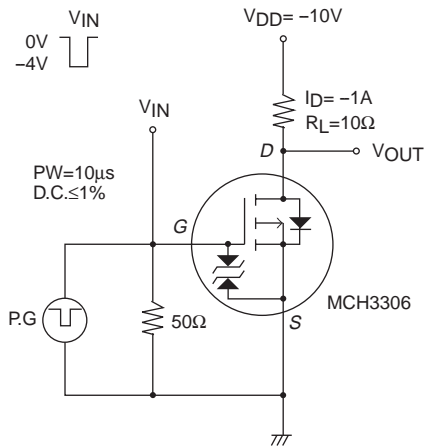


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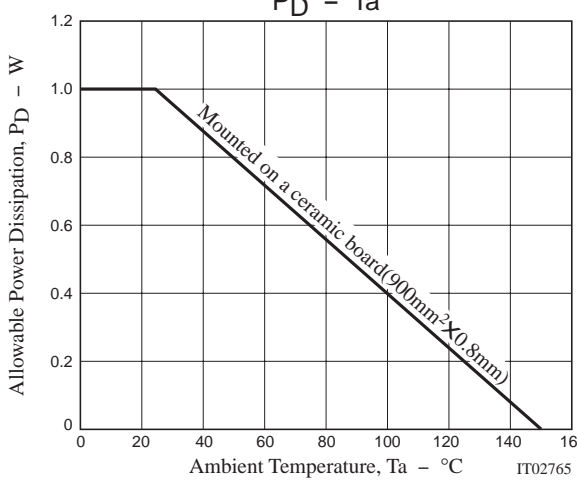
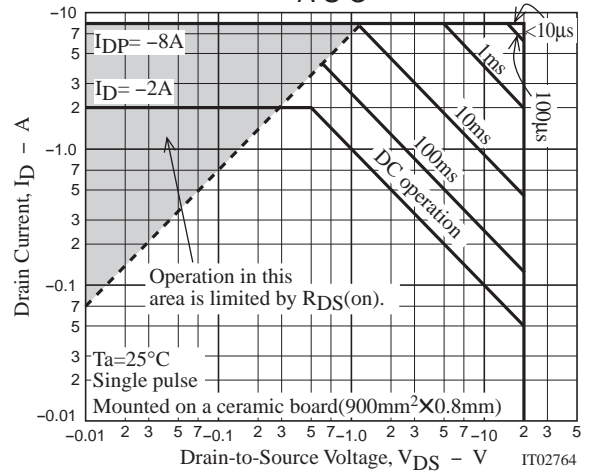
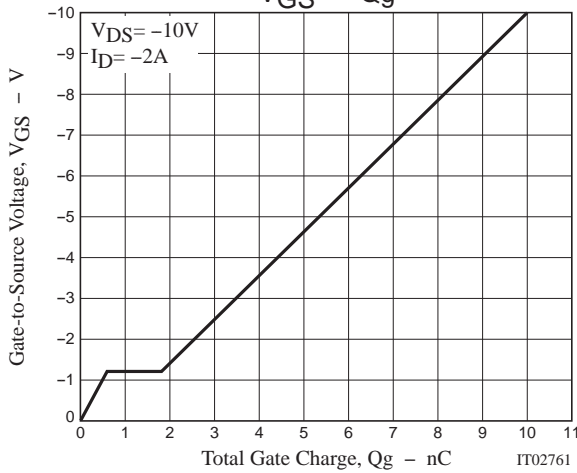
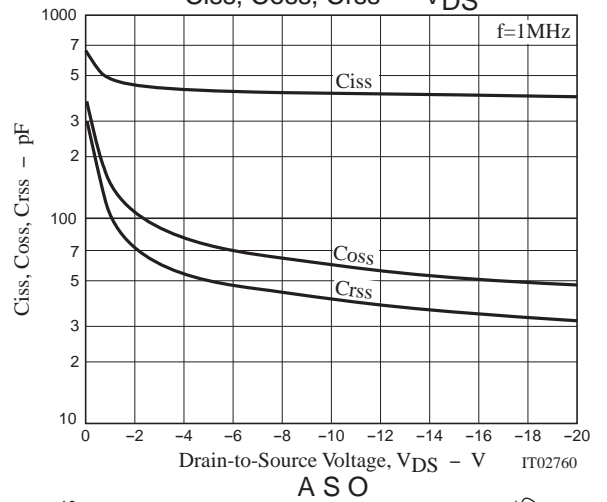
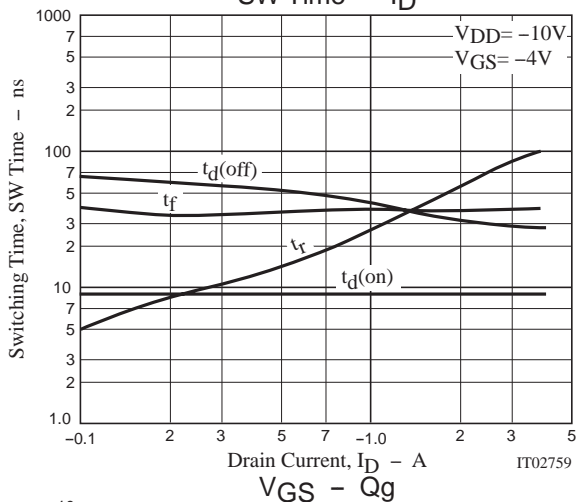
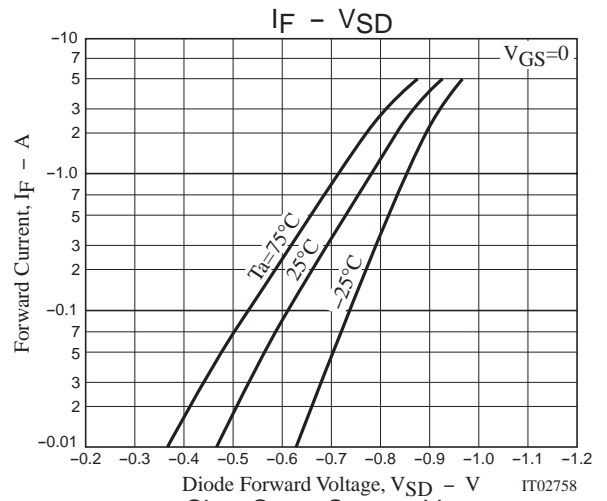
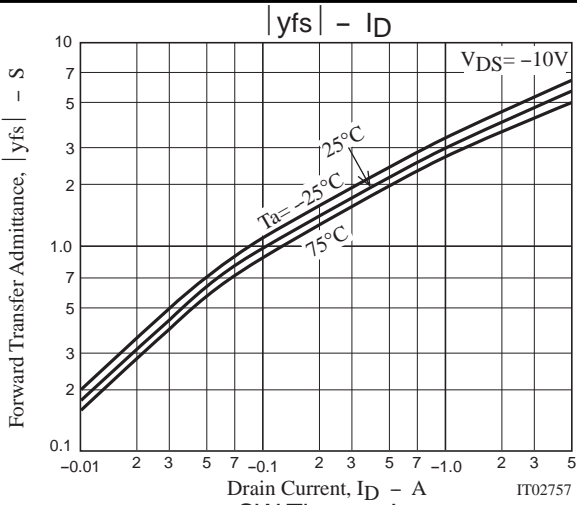
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	$C_{iss}$	$V_{DS}=-10V, f=1MHz$		410		pF
Output Capacitance	$C_{oss}$	$V_{DS}=-10V, f=1MHz$		60		pF
Reverse Transfer Capacitance	$C_{rss}$	$V_{DS}=-10V, f=1MHz$		40		pF
Turn-ON Delay Time	$t_d(on)$	See specified Test Circuit		9		ns
Rise Time	$t_r$	See specified Test Circuit		27		ns
Turn-OFF Delay Time	$t_d(off)$	See specified Test Circuit		42		ns
Fall Time	$t_f$	See specified Test Circuit		38		ns
Total Gate Charge	$Q_g$	$V_{DS}=-10V, V_{GS}=-10V, I_D=-2A$		10		nC
Gate-to-Source Charge	$Q_{gs}$	$V_{DS}=-10V, V_{GS}=-10V, I_D=-2A$		0.6		nC
Gate-to-Drain "Miller" Charge	$Q_{gd}$	$V_{DS}=-10V, V_{GS}=-10V, I_D=-2A$		1.2		nC
Diode Forward Voltage	$V_{SD}$	$I_S=-2A, V_{GS}=0$		-0.88	-1.2	V

## Switching Time Test Circuit



# MCH3306



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